

L A Coldren

List of Publications by Citations

Source: <https://exaly.com/author-pdf/11819782/l-a-coldren-publications-by-citations.pdf>

Version: 2024-04-24

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

155
papers

5,971
citations

41
h-index

72
g-index

164
ext. papers

6,660
ext. citations

3.6
avg, IF

4.95
L-index

#	Paper	IF	Citations
155	Picosecond coherent optical manipulation of a single electron spin in a quantum dot. <i>Science</i> , 2008 , 320, 349-52	33.3	402
154	Effective band gap inhomogeneity and piezoelectric field in InGaN/GaN multiquantum well structures. <i>Applied Physics Letters</i> , 1998 , 73, 2006-2008	3.4	380
153	Optical anisotropy in a quantum-well-wire array with two-dimensional quantum confinement. <i>Physical Review Letters</i> , 1989 , 62, 466-469	7.4	354
152	Two-dimensional free-space beam steering with an optical phased array on silicon-on-insulator. <i>Optics Express</i> , 2011 , 19, 21595-604	3.3	221
151	Indium tin oxide contacts to gallium nitride optoelectronic devices. <i>Applied Physics Letters</i> , 1999 , 74, 3930-3932	3.4	187
150	Extremely wide modulation bandwidth in a low threshold current strained quantum well laser. <i>Applied Physics Letters</i> , 1988 , 53, 1378-1380	3.4	185
149	Fully integrated hybrid silicon two dimensional beam scanner. <i>Optics Express</i> , 2015 , 23, 5861-74	3.3	182
148	Surface migration induced self-aligned InAs islands grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995 , 66, 1620-1622	3.4	162
147	Nondestructive optical measurements of a single electron spin in a quantum dot. <i>Science</i> , 2006 , 314, 1916-20	33.3	151
146	Growth and characterization of bulk InGaN films and quantum wells. <i>Applied Physics Letters</i> , 1996 , 68, 3147-3149	3.4	142
145	Measured and calculated radiative lifetime and optical absorption of In _x Ga _{1-x} N/GaN quantum structures. <i>Physical Review B</i> , 2000 , 61, 10994-11008	3.3	128
144	Monolithic two-section GaInAsP/InP active-optical-resonator devices formed by reactive ion etching. <i>Applied Physics Letters</i> , 1981 , 38, 315-317	3.4	119
143	Theoretical gain in strained InGaAs/AlGaAs quantum wells including valence-band mixing effects. <i>Applied Physics Letters</i> , 1990 , 57, 2835-2837	3.4	116
142	Optically detected coherent spin dynamics of a single electron in a quantum dot. <i>Nature Physics</i> , 2007 , 3, 770-773	16.2	112
141	Spontaneous growth of coherent tilted superlattice on vicinal (100) GaAs substrates. <i>Applied Physics Letters</i> , 1989 , 54, 1690-1692	3.4	100
140	GaInAsP/InP stripe-geometry laser with a reactive-ion-etched facet. <i>Applied Physics Letters</i> , 1980 , 37, 681-683	3.4	95
139	Band-gap engineered digital alloy interfaces for lower resistance vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 1993 , 63, 3411-3413	3.4	78

138	Large and small signal dynamics of vertical cavity surface emitting lasers. <i>Applied Physics Letters</i> , 1993 , 62, 325-327	3.4	75
137	Externally mode-matched cavity quantum electrodynamics with charge-tunable quantum dots. <i>Physical Review Letters</i> , 2009 , 102, 097403	7.4	63
136	Effects of Si-doping in the barriers of InGaN multiquantum well purplish-blue laser diodes. <i>Applied Physics Letters</i> , 1998 , 73, 496-498	3.4	63
135	Minimum temperature sensitivity of 1.55 μ m vertical-cavity lasers at 80 nm gain offset. <i>Applied Physics Letters</i> , 1998 , 72, 1814-1816	3.4	62
134	Lateral carrier diffusion and surface recombination in InGaAs/AlGaAs quantum-well ridge-waveguide lasers. <i>Journal of Applied Physics</i> , 1994 , 76, 4479-4487	2.5	61
133	Demonstration of broadband tunability in a semiconductor laser using sampled gratings. <i>Applied Physics Letters</i> , 1992 , 60, 2321-2323	3.4	61
132	Self-electro-optic device based on a superlattice asymmetric Fabry-Pérot modulator with an on/off ratio \approx 100:1. <i>Applied Physics Letters</i> , 1990 , 57, 1345-1347	3.4	59
131	Single-mode operation of coupled-cavity GaInAsP/InP semiconductor lasers. <i>Applied Physics Letters</i> , 1983 , 42, 6-8	3.4	58
130	Estimation of scattering losses in dielectrically apertured vertical cavity lasers. <i>Applied Physics Letters</i> , 1996 , 68, 1757-1759	3.4	57
129	Directional reactive ion etching at oblique angles. <i>Applied Physics Letters</i> , 1980 , 36, 583-585	3.4	57
128	Electrorefraction in GaAs and InGaAsP and its application to phase modulators. <i>Journal of Applied Physics</i> , 1987 , 61, 2430-2433	2.5	56
127	Reactive ion beam etching of InP with Cl ₂ . <i>Applied Physics Letters</i> , 1981 , 38, 264-266	3.4	56
126	Improved characteristics of InGaN multiple-quantum-well laser diodes grown on laterally epitaxially overgrown GaN on sapphire. <i>Applied Physics Letters</i> , 2000 , 76, 529-531	3.4	55
125	Chemical Mechanical Polishing of Gallium Nitride. <i>Electrochemical and Solid-State Letters</i> , 2002 , 5, G61		54
124	Analysis of multielement semiconductor lasers. <i>Journal of Applied Physics</i> , 1983 , 54, 2962-2969	2.5	53
123	Gain spectroscopy on InGaN/GaN quantum well diodes. <i>Applied Physics Letters</i> , 1997 , 70, 2580-2582	3.4	51
122	Two-Dimensional Optical Beam Steering With InP-Based Photonic Integrated Circuits. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 6100212-6100212	3.8	48
121	Normally-off high-contrast asymmetric Fabry-Pérot reflection modulator using Wannier-Stark localization in a superlattice. <i>Applied Physics Letters</i> , 1990 , 56, 1886-1888	3.4	47

120	Surface energy model for the thickness dependence of the lateral oxidation of AlAs. <i>Journal of Applied Physics</i> , 1997 , 82, 2277-2280	2.5	46
119	High modulation efficiency of intracavity contacted vertical cavity lasers. <i>Applied Physics Letters</i> , 1994 , 65, 1483-1485	3.4	46
118	Directional reactive-ion-etching of InP with Cl ₂ containing gases. <i>Journal of Vacuum Science and Technology</i> , 1981 , 19, 225-230		45
117	Hybrid III/V silicon photonic source with integrated 1D free-space beam steering. <i>Optics Letters</i> , 2012 , 37, 4257-9	3	43
116	Highly efficient waveguide phase modulator for integrated optoelectronics. <i>Applied Physics Letters</i> , 1986 , 48, 1243-1245	3.4	43
115	Electrically tunable Fabry-Perot mirror using multiple quantum well index modulation. <i>Applied Physics Letters</i> , 1988 , 53, 637-639	3.4	42
114	Epitaxially-stacked multiple-active-region 1.55 μm lasers for increased differential efficiency. <i>Applied Physics Letters</i> , 1999 , 74, 3251-3253	3.4	41
113	Technique for integration of vertical cavity lasers and resonant photodetectors. <i>Applied Physics Letters</i> , 1998 , 73, 1-3	3.4	40
112	Parallel free-space optical interconnect based on arrays of vertical-cavity lasers and detectors with monolithic microlenses. <i>Applied Optics</i> , 1998 , 37, 2811-21	1.7	38
111	Theoretical gain in compressive and tensile strained InGaAs/InGaAsP quantum wells. <i>Applied Physics Letters</i> , 1991 , 59, 588-590	3.4	37
110	88 °C, continuous-wave operation of apertured, intracavity contacted, 1.55 μm vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 2001 , 78, 1337-1339	3.4	36
109	High-efficiency TEM ₀₀ continuous-wave (Al,Ga)As epitaxial surface-emitting lasers and effect of half-wave periodic gain. <i>Applied Physics Letters</i> , 1989 , 54, 1209-1211	3.4	36
108	Evaluating the effects of optical and carrier losses in etched-post vertical cavity lasers. <i>Journal of Applied Physics</i> , 1995 , 78, 5871-5875	2.5	35
107	MONOLITHIC ACOUSTIC SURFACE-WAVE AMPLIFIER. <i>Applied Physics Letters</i> , 1971 , 18, 317-319	3.4	34
106	Near-room-temperature continuous-wave operation of multiple-active-region 1.55 μm vertical-cavity lasers with high differential efficiency. <i>Applied Physics Letters</i> , 2000 , 77, 3137-3139	3.4	32
105	Dielectric apertures as intracavity lenses in vertical-cavity lasers. <i>Applied Physics Letters</i> , 1996 , 68, 313-315	3.4	32
104	On the Formation of Planar-Etched Facets in GaInAsP / InP Double Heterostructures. <i>Journal of the Electrochemical Society</i> , 1983 , 130, 1918-1926	3.9	32
103	. <i>Journal of Lightwave Technology</i> , 2013 , 31, 2244-2253	4	31

102	Design parameters for lateral carrier confinement in quantum-dot lasers. <i>Applied Physics Letters</i> , 1999 , 74, 2752-2754	3.4	31
101	Transverse modulators with a record reflection change of >20%/V using asymmetric FabryPerot structures. <i>Applied Physics Letters</i> , 1990 , 56, 1626-1628	3.4	31
100	Disordering of GaAs/AlGaAs multiple quantum well structures by thermal annealing for monolithic integration of laser and phase modulator. <i>Applied Physics Letters</i> , 1989 , 55, 672-674	3.4	30
99	Terahertz electro-optic wavelength conversion in GaAs quantum wells: Improved efficiency and room-temperature operation. <i>Applied Physics Letters</i> , 2004 , 84, 840-842	3.4	28
98	Voltage-controlled wavelength conversion by terahertz electro-optic modulation in double quantum wells. <i>Applied Physics Letters</i> , 2002 , 81, 1564-1566	3.4	27
97	Room-temperature two-dimension exciton exchange and blue shift of absorption edge in GaAs/AlGaAs superlattices under an electric field. <i>Applied Physics Letters</i> , 1989 , 54, 1549-1551	3.4	27
96	Modeling the current to light characteristics of index-guided vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 1993 , 62, 1050-1052	3.4	24
95	Efficient vertical-cavity lasers. <i>Optical and Quantum Electronics</i> , 1992 , 24, S105-S119	2.4	24
94	High-efficiency and low-threshold InGaAs/AlGaAs quantum-well lasers. <i>Journal of Applied Physics</i> , 1994 , 76, 3932-3934	2.5	23
93	Generation of picosecond pulses with a gain-switched GaAs surface-emitting laser. <i>Applied Physics Letters</i> , 1990 , 57, 963-965	3.4	23
92	Contribution of the band-filling effect to the effective refractive-index change in double-heterostructure GaAs/AlGaAs phase modulators. <i>Journal of Applied Physics</i> , 1987 , 62, 4548-4553 ^{2.5}	2.5	23
91	Effect of bias field in a zinc-oxide-on-silicon acoustic convolver. <i>Applied Physics Letters</i> , 1974 , 25, 473-475 ^{3.4}	3.4	22
90	Calibrated intensity noise measurements in microcavity laser diodes. <i>Applied Physics Letters</i> , 1995 , 67, 3697-3699	3.4	21
89	Tertiarybutylarsine and tertiarybutylphosphine for the MOCVD growth of low threshold 1.55 μm In _x Ga _{1-x} As/InP quantum-well lasers. <i>Journal of Electronic Materials</i> , 1994 , 23, 87-91	1.9	21
88	Wide-bandwidth, high-efficiency reflection modulators using an unbalanced FabryPerot structure. <i>Applied Physics Letters</i> , 1989 , 55, 1946-1948	3.4	21
87	Many body effects in the temperature dependence of threshold in a vertical-cavity surface-emitting laser. <i>Applied Physics Letters</i> , 1995 , 66, 2460-2462	3.4	20
86	Effect of layer thickness variations on the performance of asymmetric FabryPerot reflection modulators. <i>Journal of Applied Physics</i> , 1992 , 72, 855-860	2.5	20
85	Tight-binding analysis on exciton binding energy in field-induced Stark-localized superlattices. <i>Applied Physics Letters</i> , 1989 , 55, 2002-2004	3.4	19

84	Temperature-dependent threshold and modulation characteristics in InGaAs/GaAs quantum-well ridge-waveguide lasers. <i>Applied Physics Letters</i> , 1995 , 66, 2040-2042	3.4	18
83	Acoustic waveguide with a cladded core geometry. <i>Applied Physics Letters</i> , 1975 , 26, 31-34	3.4	18
82	Electronically variable delay using ferroelastic-ferroelectrics. <i>Applied Physics Letters</i> , 1977 , 30, 506-508	3.4	18
81	Optical gain anisotropy in serpentine superlattice nanowire-array lasers. <i>Applied Physics Letters</i> , 1993 , 63, 2015-2017	3.4	17
80	GaAs/AlGaAs multiple quantum well field-induced optical waveguide. <i>Applied Physics Letters</i> , 1990 , 57, 114-116	3.4	17
79	Design of optimized high-speed depletion-edge-translation optical waveguide modulators in III-V semiconductors. <i>Applied Physics Letters</i> , 1987 , 51, 792-794	3.4	17
78	cw monolithic acoustic surface wave amplifier incorporated in a $\lambda/4$ waveguide. <i>Applied Physics Letters</i> , 1973 , 23, 117-118	3.4	17
77	Reduced lateral carrier diffusion for improved miniature semiconductor lasers. <i>Journal of Applied Physics</i> , 1997 , 81, 3377-3381	2.5	16
76	Resonant-cavity InGaAs/InAlGaAs/InP photodetector arrays for wavelength demultiplexing applications. <i>Applied Physics Letters</i> , 1997 , 70, 2347-2349	3.4	16
75	Strong-field terahertz optical mixing in excitons. <i>Physical Review B</i> , 2003 , 67,	3.3	16
74	Analysis and optimization of graded-index separate-confinement heterostructure waveguides for quantum well lasers. <i>Journal of Applied Physics</i> , 1991 , 69, 2857-2861	2.5	16
73	Optimum coupling junction and cavity lengths for coupled-cavity semiconductor lasers. <i>Journal of Applied Physics</i> , 1985 , 57, 740-754	2.5	16
72	Stabilization and optimum biasing of dynamic-single-mode coupled-cavity lasers. <i>Applied Physics Letters</i> , 1984 , 44, 169-171	3.4	15
71	Cleaved-coupled-cavity lasers with large cavity length ratios for enhanced stability. <i>Applied Physics Letters</i> , 1984 , 44, 821-823	3.4	15
70	Molecular-beam epitaxy growth of high-quality active regions with strained In _x Ga _{1-x} As quantum wells and lattice-matched Al _x Ga _{1-x} InAs barriers using submonolayer superlattices. <i>Applied Physics Letters</i> , 2002 , 80, 3509-3511	3.4	14
69	Low regrowth interface recombination rates in InGaAs/GaAs buried ridge lasers fabricated by in situ processing. <i>Applied Physics Letters</i> , 1995 , 66, 1966-1968	3.4	14
68	Optically addressed spatial light modulators by MBE-grown nipi MQW structures. <i>Applied Optics</i> , 1989 , 28, 4801-7	1.7	14
67	Effect of temperature on the operating characteristics of asymmetric Fabry-Perot reflection modulators. <i>Applied Physics Letters</i> , 1990 , 57, 267-269	3.4	14

66	Zinc-oxide on silicon acoustically scanned imager with positive sensitivity and storage capabilities. <i>Applied Physics Letters</i> , 1975 , 27, 6-8	3-4	14
65	Terahertz optical mixing in biased GaAs single quantum wells. <i>Physical Review B</i> , 2004 , 70,	3-3	13
64	Observation of anomalously large blue shift of the heavy-hole photocurrent peak and optical bistability in narrow asymmetric coupled quantum wells. <i>Applied Physics Letters</i> , 1991 , 59, 1025-1027	3-4	13
63	Low-threshold high-efficiency high-yield impurity-induced layer disordering laser by self-aligned Si-Zn diffusion. <i>Applied Physics Letters</i> , 1990 , 57, 2534-2536	3-4	13
62	Radical beam/ion beam etching of GaAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988 , 6, 1885		13
61	. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-14	1.8	12
60	Design, fabrication and characterization of high-speed asymmetric Fabry-Perot modulators for optical interconnect applications. <i>Optical and Quantum Electronics</i> , 1993 , 25, S885-S898	2.4	12
59	Continuous operation of monolithic dynamic-single-mode coupled-cavity lasers. <i>Applied Physics Letters</i> , 1984 , 44, 368-370	3-4	12
58	Reconfigurable optical properties in InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , 1997 , 71, 1455-1457	3.4	11
57	Terahertz-optical mixing in undoped and doped GaAs quantum wells: From excitonic to electronic intersubband transitions. <i>Physical Review B</i> , 2005 , 72,	3-3	11
56	Photonic integrated tunable receivers with optical preamplifiers for direct detection. <i>Applied Physics Letters</i> , 1993 , 63, 880-882	3-4	11
55	Optically controlled reflection modulator using GaAs-AlGaAs n-i-p-i/multiple-quantum-well structures. <i>Optics Letters</i> , 1989 , 14, 230-2	3	11
54	Continuous tunability in three-terminal coupled-cavity lasers. <i>Applied Physics Letters</i> , 1986 , 48, 1190-1192	3.4	11
53	Zinc oxide on silicon memory cells scanned by acoustic surface waves. <i>Applied Physics Letters</i> , 1975 , 26, 137-139	3-4	11
52	Behavior of SiN _x films as masks for Zn diffusion. <i>Journal of Applied Physics</i> , 1987 , 62, 828-831	2.5	10
51	Reduced dynamic linewidth in three-terminal two-section diode lasers. <i>Applied Physics Letters</i> , 1985 , 46, 125-127	3-4	10
50	Variable frequency SAW resonators on ferroelectric-ferroelastics. <i>Applied Physics Letters</i> , 1978 , 32, 129-131	3.4	10
49	Coupled-cavity resonant photodetectors for high-performance wavelength demultiplexing applications. <i>Applied Physics Letters</i> , 1997 , 71, 178-180	3-4	9

48	Measurement of gain current relations for InGaN multiple quantum wells. <i>Applied Physics Letters</i> , 1998 , 73, 3887-3889	3-4	9
47	Silicon diffusion into Al _x Ga _{1-x} As (x=0.4) from a sputtered silicon film. <i>Applied Physics Letters</i> , 1987 , 50, 265-266	3-4	9
46	Interior-surface acoustic waveguiding in capillaries. <i>Applied Physics Letters</i> , 1974 , 25, 324-326	3-4	9
45	Analog read-only memory using gadolinium molybdate. <i>Applied Physics Letters</i> , 1978 , 33, 373-375	3-4	9
44	Fully integrated hybrid silicon free-space beam steering source with 32-channel phased array 2014 ,		8
43	Molecular beam epitaxial growth of monolithic 1.55 μ m vertical cavity surface emitting lasers with AlGaAsSb/AlAsSb Bragg mirrors. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 1601		8
42	Effect of AlGa _N /Ga _N Strained Layer Superlattice Period on InGa _N MQW Laser Diodes. <i>Physica Status Solidi A</i> , 1999 , 176, 59-62		8
41	High-contrast, large optical bandwidth field-induced guide/antiguide modulator. <i>Applied Physics Letters</i> , 1991 , 58, 2211-2213	3-4	8
40	High-differential-quantum-efficiency, long-wavelength vertical-cavity lasers using five-stage bipolar-cascade active regions. <i>Applied Physics Letters</i> , 2005 , 86, 2111-1104	3-4	7
39	Catastrophic optical damage in GaInN multiple quantum wells. <i>Applied Physics Letters</i> , 1998 , 72, 3267-3269	3-4	7
38	Use of independently controlled Cl radical and Ar ion beams for anisotropic chemically enhanced etching of GaAs. <i>Applied Physics Letters</i> , 1988 , 53, 2308-2310	3-4	7
37	Etched-groove coupled-cavity vapor-phase-transported window lasers at 1.55 μ m. <i>Applied Physics Letters</i> , 1985 , 46, 5-7	3-4	7
36	Selectively etched tunnel junction for lateral current and optical confinement in InP-based vertical cavity lasers. <i>Journal of Electronic Materials</i> , 2004 , 33, 118-122	1-9	6
35	Al _{0.95} Ga _{0.05} As _{0.56} Sb _{0.44} for lateral oxide-confinement layer in InP-based devices. <i>Applied Physics Letters</i> , 2003 , 82, 1329-1331	3-4	6
34	Enhanced wavelength tuning of an InGaAsP-InP laser with a thermal-strain-magnifying trench. <i>Applied Physics Letters</i> , 2000 , 77, 2629-2631	3-4	6
33	Analysis and optimization of quantum-well thickness for GaAs/AlGaAs and InGaAs/GaAs/AlGaAs quantum-well lasers. <i>Journal of Applied Physics</i> , 1992 , 72, 5047-5054	2-5	6
32	Impurity-induced-disordered phase modulators in AlGaAs/GaAs quantum well and double-heterostructure waveguides. <i>Applied Physics Letters</i> , 1988 , 53, 728-730	3-4	6
31	Self-aligned Si-Zn diffusion into GaAs and AlGaAs. <i>Journal of Applied Physics</i> , 1988 , 64, 1855-1858	2-5	6

30	Optoelectronic properties of coupled cavity semiconductor lasers. <i>Applied Physics Letters</i> , 1984 , 44, 735-737	3.4	6
29	TRAPPING MODEL FOR InSb THIN FILMS. <i>Applied Physics Letters</i> , 1971 , 18, 319-321	3.4	6
28	Relating the chirp parameter to the number of quantum wells in GaAs/AlGaAs waveguide modulators. <i>Applied Physics Letters</i> , 1989 , 55, 718-720	3.4	5
27	A monolithic diode laser chemical sensor with a quasi-symmetrical sensing waveguide for improved sensitivity. <i>Applied Physics Letters</i> , 2004 , 85, 320-322	3.4	4
26	Increased lateral oxidation rates of AlInAs on InP using short-period superlattices. <i>Journal of Electronic Materials</i> , 2000 , 29, 1100-1104	1.9	4
25	Rate equations of vertical-cavity semiconductor optical amplifiers. <i>Applied Physics Letters</i> , 2002 , 80, 3057-3059	3.4	3
24	Measurement of the AlGaInAs/AlGaAs conduction-band offset using ballistic electron emission spectroscopy. <i>Applied Physics Letters</i> , 1998 , 73, 3271-3272	3.4	3
23	Effects of surface recombination on carrier distributions and device characteristics. <i>Journal of Applied Physics</i> , 1995 , 78, 3208-3215	2.5	3
22	Intensity noise and facet correlation in Fabry-Pérot laser diodes with low facet reflectivities. <i>Applied Physics Letters</i> , 1995 , 66, 3419-3421	3.4	3
21	Molecular beam epitaxial growth of strained AlGaInAs multi-quantum well lasers on InP. <i>Journal of Electronic Materials</i> , 1996 , 25, 948-954	1.9	3
20	Simultaneous gain and phase-shift enhancements in periodic gain structures. <i>Journal of Applied Physics</i> , 1990 , 67, 4387-4389	2.5	3
19	Asymmetric Fabry-Pérot reflection modulators using red- and blue-shifted electroabsorption effects. <i>Journal of Applied Physics</i> , 1990 , 68, 875-877	2.5	3
18	Dry Etching and Impurity Diffusion for Integrated Optoelectronics. <i>Materials Research Society Symposia Proceedings</i> , 1988 , 126, 237		3
17	Single-chip dual-pumped SOA-based phase-sensitive amplifier at 1550nm 2015 ,		2
16	Photoluminescence characteristics of GaN/InGaN/GaN quantum wells. <i>Journal of Electronic Materials</i> , 1997 , 26, 325-329	1.9	2
15	Individually optimized bottom-emitting vertical-cavity lasers and bottom-illuminated resonant photodetectors sharing the same epitaxial structure. <i>Journal of Optics</i> , 1999 , 1, 317-319		2
14	InP-based multiple quantum well structures grown with tertiarybutylarsine (TBA) and tertiarybutylphosphine (TBP): Effects of growth interruptions on structural and optical properties. <i>Journal of Electronic Materials</i> , 1996 , 25, 965-971	1.9	2
13	Effects of Hydrogen on Chlorine Radical-Beam Ion-Beam Etching of Al _x Ga _{1-x} As with Varying Mole Fraction. <i>Journal of the Electrochemical Society</i> , 1993 , 140, 1802-1804	3.9	2

12	Comparison of quantum-confined Stark effect in interdiffused and abrupt GaAs/AlGaAs quantum wells. <i>Applied Physics Letters</i> , 1989 , 55, 2526-2528	3.4	2
11	Compound-Cavity Lasers For Medium Range Lidar Applications 1989 ,		2
10	Sputtered silicon as a new etching mask for GaAs devices. <i>Journal of Applied Physics</i> , 1986 , 60, 1218-1220.	2.5	2
9	30 Gbps bottom-emitting 1060 nm VCSEL 2014 ,		1
8	Hybrid silicon free-space source with integrated beam steering 2013 ,		1
7	Fabrication and molecular beam epitaxy regrowth of first-order, high contrast AlGaAs/InGaAs gratings. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1559		1
6	High Performance Quantum Well Asymmetric Fabry-Perot Reflection Modulators: Effect of Layer Thickness Variations. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 240, 609		0
5	Introduction to the Issue on Semiconductor Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2007 , 13, 1043-1045	3.8	
4	Vertical-cavity surface-emitting lasers for free-space interconnects 1996 , 10284, 8		
3	Characterization of geometric effects for the guide/antiguide intensity modulator. <i>Journal of Applied Physics</i> , 1992 , 72, 4455-4457	2.5	
2	Guide/antiguide optical intensity modulator. <i>Optical and Quantum Electronics</i> , 1993 , 25, S899-S915	2.4	
1	Real-time technique for the characterization of tunable single-frequency lasers. <i>Applied Physics Letters</i> , 1988 , 52, 2217-2219	3.4	